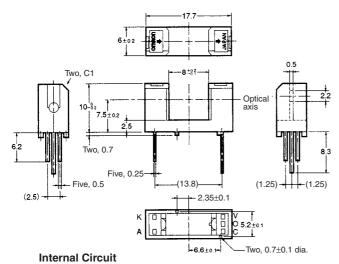
Photomicrosensor (Transmissive) **EE-SX3070/-SX4070**

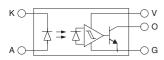


Be sure to read Precautions on page 25.

■ Dimensions

Note: All units are in millimeters unless otherwise indicated.





Terminal No.	Name
Α	Anode
K	Cathode
V	Power supply (Vcc)
0	Output (OUT)
G	Ground (GND)

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance	
3 mm max.	±0.3	
3 < mm ≤ 6	±0.375	
6 < mm ≤ 10	±0.45	
10 < mm ≤ 18	±0.55	
18 < mm ≤ 30	±0.65	

■ Features

- Incorporates an IC chip with a built-in detector element and amplifier.
- Incorporates a detector element with a built-in temperature compensation circuit.
- A wide supply voltage range: 4.5 to 16 VDC
- Directly connects with C-MOS and TTL.
- High resolution with a 0.5-mm-wide sensing aperture.
- Dark ON model (EE-SX3070)
- Light ON model (EE-SX4070)

■ Absolute Maximum Ratings (Ta = 25°C)

	Item	Symbol	Rated value
Emitter	Forward current	I _F	50 mA (see note 1)
	Reverse voltage	V_R	4 V
Detector	Power supply voltage	V _{cc}	16 V
	Output voltage	V_{OUT}	28 V
	Output current	I _{OUT}	16 mA
	Permissible output dissipation	P _{OUT}	250 mW (see note 1)
Ambient tem- perature	Operating	Topr	–40°C to 75°C
	Storage	Tstg	–40°C to 85°C
Soldering temperature		Tsol	260°C (see note 2)

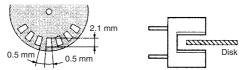
Note: 1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.

2. Complete soldering within 10 seconds.

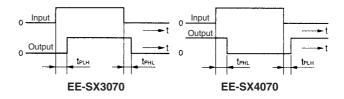
■ Electrical and Optical Characteristics (Ta = 25°C)

	Item	Symbol	Value	Condition	
Emitter	Forward voltage	V_{F}	1.2 V typ., 1.5 V max.	I _F = 20 mA	
	Reverse current	I _R	0.01 μA typ., 10 μA max.	V _R = 4 V	
	Peak emission wave- length	λ_{P}	940 nm typ.	I _F = 20 mA	
Detector Low-level output voltage	Low-level output voltage	V _{OL}	0.12 V typ., 0.4 V max.	V_{CC} = 4.5 to 16 V, I_{OL} = 16 mA, I_F = 0 mA (EE-SX3070), I_F = 10 mA (EE-SX4070)	
	High-level output volt- age	V _{OH}	15 V min.	V_{CC} = 16 V, R_L = 1 k Ω , I_F = 10 mA (EE-SX3070), I_F = 0 mA (EE-SX4070)	
	Current consumption	I _{cc}	3.2 mA typ., 10 mA max.	V _{CC} = 16 V	
	Peak spectral sensitivity wavelength	λ_{P}	870 nm typ.	V _{CC} = 4.5 to 16 V	
LED currer	nt when output is OFF	I _{FT}	10 mA max.	V _{CC} = 4.5 to 16 V	
LED currer	nt when output is ON				
Hysteresis		ΔΗ	15% typ.	V _{CC} = 4.5 to 16 V (see note 1)	
Response	frequency	f	3 kHz min.	$V_{CC} = 4.5 \text{ to } 16 \text{ V}, I_F = 20 \text{ mA}, I_{OL} = 16 \text{ mA (see note 2)}$	
Response	delay time	t _{PLH} (t _{PHL})	3 μs typ.	V_{CC} = 4.5 to 16 V, I_F = 20 mA, I_{OL} = 16 mA (see note 3)	
Response	delay time	t _{PHL} (t _{PLH})	20 μs typ.	V_{CC} = 4.5 to 16 V, I_F = 20 mA, I_{OL} = 16 mA (see note 3)	

- Note: 1. Hysteresis denotes the difference in forward LED current value, expressed in percentage, calculated from the respective forward LED currents when the photo IC in turned from ON to OFF and when the photo IC in turned from OFF to ON.
 - 2. The value of the response frequency is measured by rotating the disk as shown below.



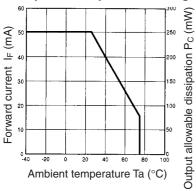
The following illustrations show the definition of response delay time. The value in the parentheses applies to the EE-SX4070.



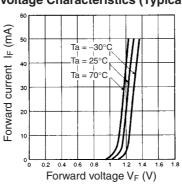
■ Engineering Data

Note: The values in the parentheses apply to the EE-SX4070.

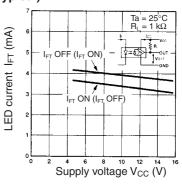
Forward Current vs. Collector Dissipation Temperature Rating



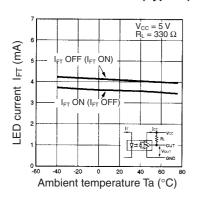
Forward Current vs. Forward Voltage Characteristics (Typical)



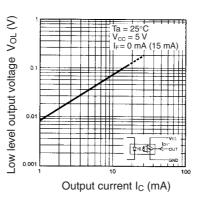
LED Current vs. Supply Voltage (Typical)



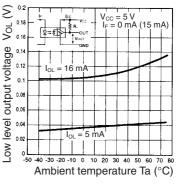
LED Current vs. Ambient Temperature Characteristics (Typical)



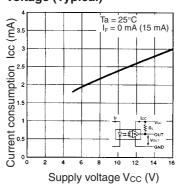
Low-level Output Voltage vs. Output Current (Typical)



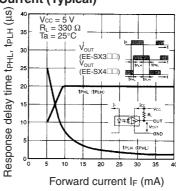
Low-level Output Voltage vs. Ambient Temperature Characteristics (Typical)



Current Consumption vs. Supply Voltage (Typical)



Response Delay Time vs. Forward Current (Typical)



Repeat Sensing Position Characteristics (Typical)

